



U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

**SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENT**

Docket Number:
10746/40

Application Number
10/775,806

Filing Date
2/9/04

Examiner
Asok K. Sarkar

Art Unit
2829

Title
**SEMICONDUCTOR OPTICAL DEVICE
AND THE FABRICATION METHOD**

Applicant(s)
Susumu KONDO et al.

Address to
Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

1. In accordance with the duty of disclosure under 37 C.F.R. § 1.56 and in conformance with the procedures of 37 C.F.R. §§ 1.97 and 1.98 and M.P.E.P. § 609, attorneys for Applicants hereby bring the following references to the attention of the Examiner. The references are listed on the attached modified PTO Form No. 1449. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.
2. A copy of each patent listed on the modified PTO form 1449 is enclosed.
3. It is hereby certified that each item of information contained in this Supplemental Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Supplemental Information Disclosure Statement.
4. While no fee is believed to be due (since there is no first Office Action on the merits), the Commissioner is authorized to charge any additional fees that may be required to the deposit account of **Kenyon & Kenyon**, deposit account number **11-0600**.

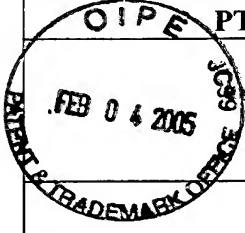
Dated: 2/8/2005

By: [Signature]

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| INFORMATION DISCLOSURE STATEMENT BY APPLICANTS  PTO FORM 1449 | ATTY. DOCKET NO. 10746/40 | SERIAL NO. 10/775,806 |
| | APPLICANT(s) S. KONDO et al. | |
| | FILING DATE 2/9/04 | GROUP 2829 |

U. S. PATENT DOCUMENTS

| EXAMINER INITIAL | PATENT NUMBER | PATENT DATE | NAME | CLASS | SUBCLASS | FILING DATE |
|---------------------|------------------|-----------------|----------------------|-------|----------|----------------|
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| | 6,011,811 | January 4, 2000 | Oehlander ULF, et al | | | |
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FOREIGN PATENT DOCUMENTS

| EXAMINER INITIAL | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUB- CLASS | TRANSLATION | |
|---------------------|--------------------|-----------------|---------|-------|---------------|---------------------|----|
| | | | | | | YES | NO |
| | 1 139 526 | October 4, 2001 | EP | | | English Document | |
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OTHER DOCUMENTS

| EXAMINER INITIAL | AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC. |
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| | European Search Report, November 22, 2004, AER/P104292EP |
| | DADGAR A et al, "Ruthenium: a superior compensator of InP," APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS. NEW YORK, US. Vol. 73, no. 26, December 28, 1998, pages 3878-3880 |
| | LOURDUDOSS S et al., "Semi-Insulating Epitaxial Layers for Optoelectronic Devices" Institute of Electrical and Electronics Engineers, 2000 International Semiconducting and Insulating Materials Conference. The Australian National University, Canberra, Australia, July 3-7, 2000, IEEE, US, vol. CONF. 11, July 3, 2000, pages 171-178. |
| | GEELEN Van et al., "RUTHENIUM DOPED HIGH POWER 1.48 MUM SIPBH LASER." 1999 11 th . International Conference on Indium Phosphide and Related Materials. Conference proceedings. IPRM DAVOS, May 16-20, 1999. IEEE, US, vol. Conf. 11, May 16, 1999, pages 203-206. |

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|---|------------------------|
| EXAMINER | DATE CONSIDERED |
| EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | |